20V P-CHANNEL ENHANCEMENT MODE MOSFET
PowerDI5060-8

Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D T_C = +25°C
-20V	6mΩ @ V_{GS} = -4.5V	-83A
	8mΩ @ V_{GS} = -2.5V	-72A

Features

- Thermally Efficient Package-Cooler Running Applications
- < 1.1mm Package Profile – Ideal for Thin Applications
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMP26M1UPSWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

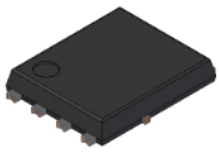
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC converters
- Load switches

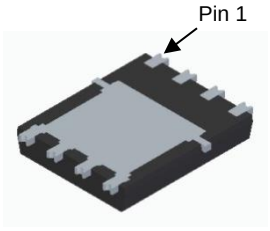
Mechanical Data

- Package: PowerDI®5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish—Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.097 grams (Approximate)

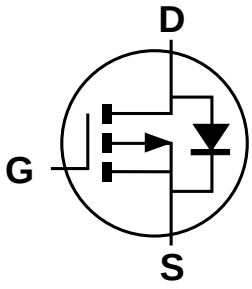
PowerDI5060-8/SWP (Type UX)



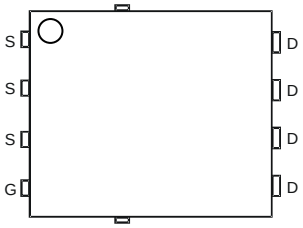
Top View



Bottom View



Internal Schematic



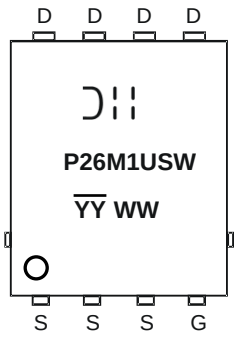
Top View
Pin Configuration

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP26M1UPSWQ-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



= Manufacturer's Marking
P26M1USW = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 23 = 2023)
WW = Week (01 to 53)

Maximum Ratings (@ T_C = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±10	V
Continuous Drain Current, V_{GS} = 10V (Note 5)	Steady State	T_C = +25°C T_C = +70°C	I_D	-83 -66	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	-2.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-134	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	-134	A
Avalanche Current, L = 0.1mH (Note 7)			I_{AS}	-33	A
Avalanche Energy, L = 0.1mH (Note 7)			E_{AS}	57	mJ

Thermal Characteristics (@ T_C = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 8)	T_A = +25°C	P_D	1.9	W
Thermal Resistance, Junction to Ambient (Note 8)		$R_{\theta JA}$	67	°C/W
Total Power Dissipation (Note 6)	T_C = +25°C	P_D	2.6	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JA}$	47	°C/W
Thermal Resistance, Junction to Case (Note 5)		$R_{\theta JC}$	2.0	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Notes:
5. Thermal resistance from junction to soldering point (on the exposed drain pad).
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Electrical Characteristics (@ T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -16V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.4	—	-1.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	4.2	6	mΩ	V_{GS} = -4.5V, I_D = -15A
		—	5.4	8		V_{GS} = -2.5V, I_D = -10A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.1	V	V_{GS} = 0V, I_S = -10A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	—	5392	—	pF	V_{DS} = -10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	608	—		
Reverse Transfer Capacitance	C_{rss}	—	564	—		
Gate Resistance	R_G	—	2.05	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	75	—	nC	V_{DD} = -10V, I_D = -20A
Total Gate Charge (V_{GS} = -10V)	Q_g	—	164	—		
Gate-Source Charge	Q_{gs}	—	6.9	—		
Gate-Drain Charge	Q_{gd}	—	19.8	—		
Turn-On Delay Time	$t_{D(ON)}$	—	9	—	ns	V_{DD} = -10V, V_{GEN} = -4.5V R_{GEN} = 1Ω, I_D = -10A
Turn-On Rise Time	t_R	—	24	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	69	—		
Turn-Off Fall Time	t_F	—	107	—		
Reverse Recovery Time	t_{RR}	—	54	—	ns	I_F = -10A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—	55	—	nC	

Notes: 9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

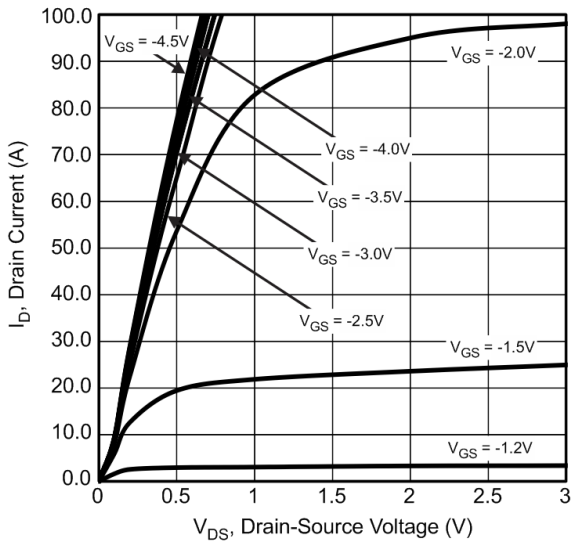


Fig. 1 Typical Output Characteristic

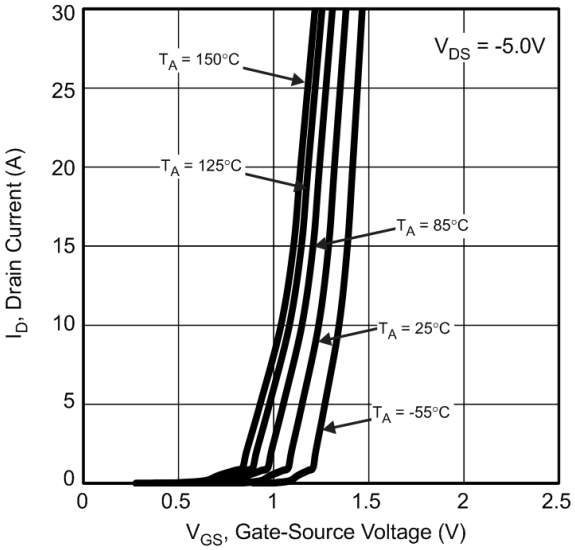


Fig. 2 Typical Transfer Characteristic

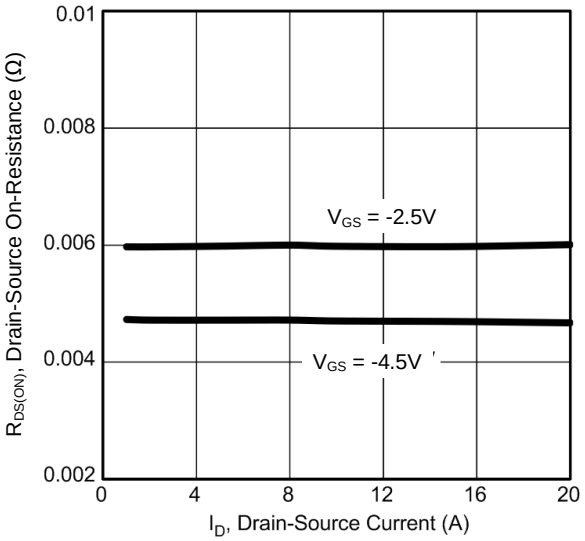


Fig. 3 Typical On-Resistance vs Drain Current and Gate Voltage

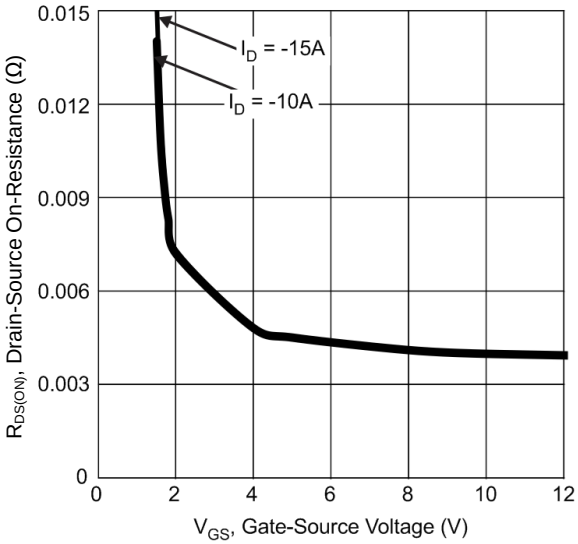


Fig. 4 Typical Transfer Characteristic

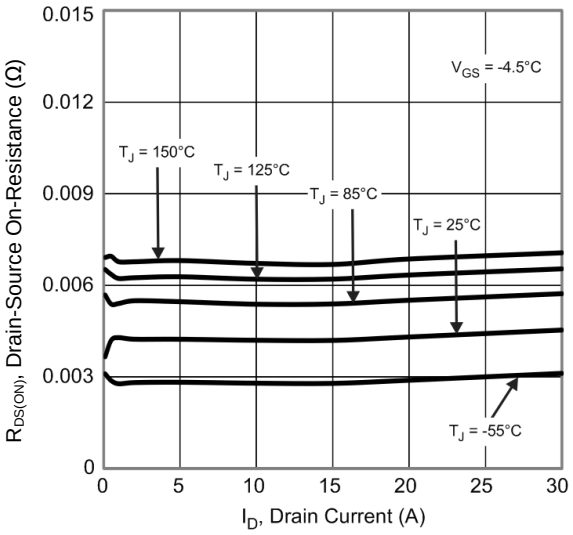


Fig. 5 Typical On-Resistance vs Drain Current and Junction Temperature

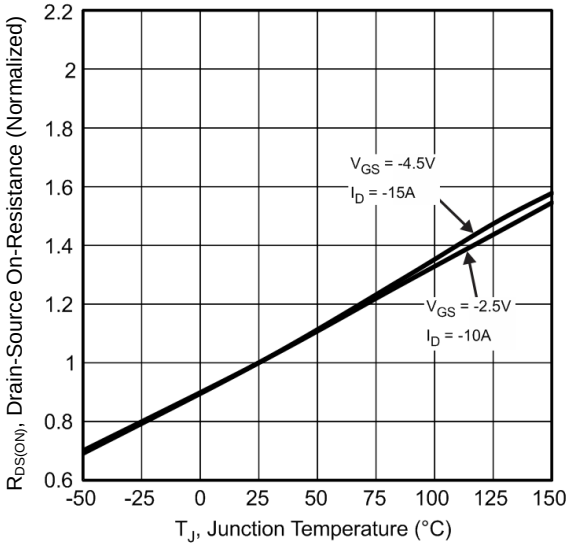


Fig. 6 On-Resistance Variation with Junction Temperature

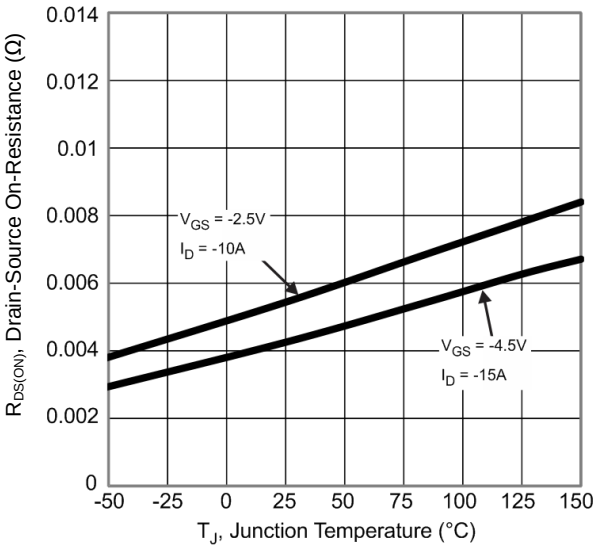


Fig. 7 On-Resistance Variation with Junction Temperature

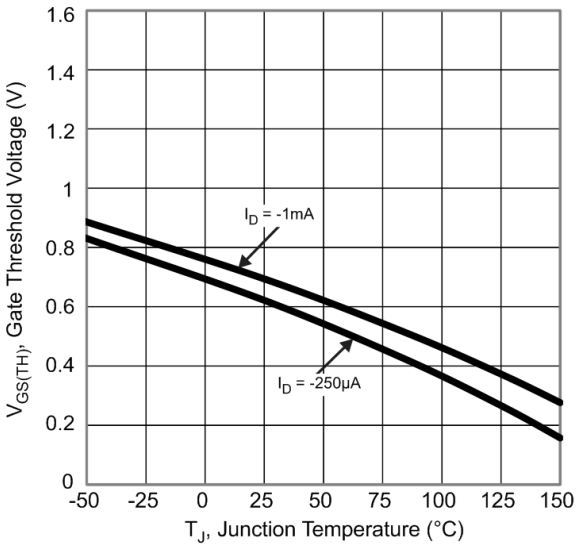


Fig. 8 Gate Threshold Variation vs Junction Temperature

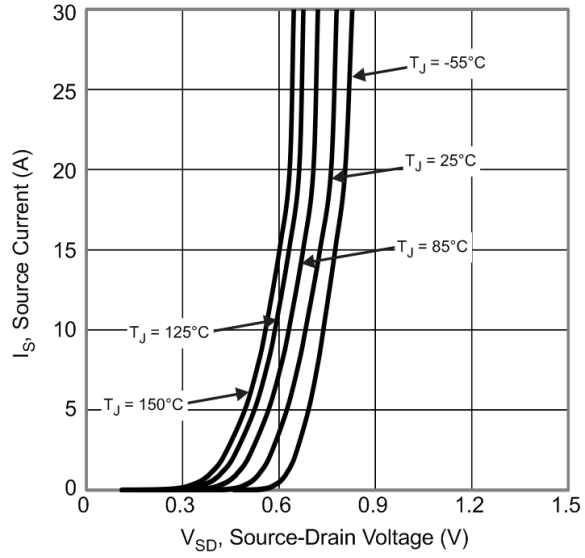


Fig. 9 Diode Forward Voltage vs Current

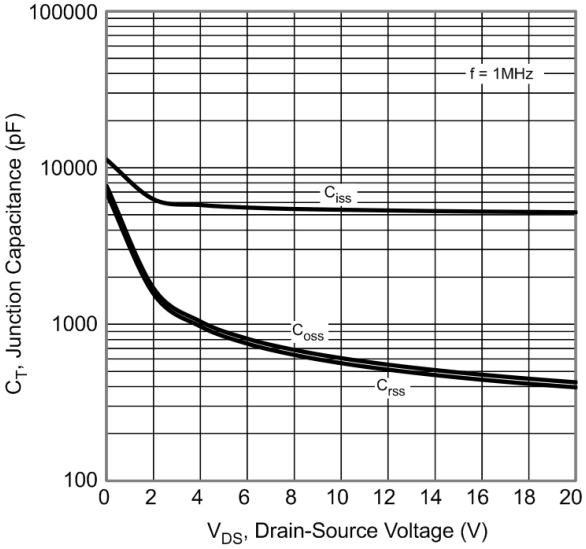


Fig. 10 Typical Junction Capacitance

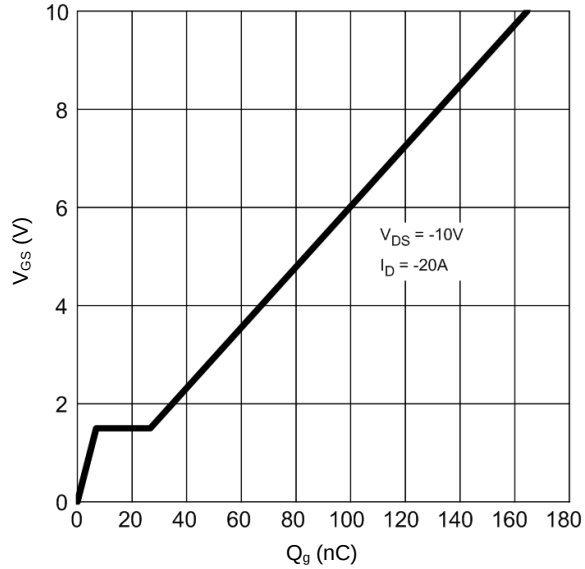


Fig. 11 Gate Charge

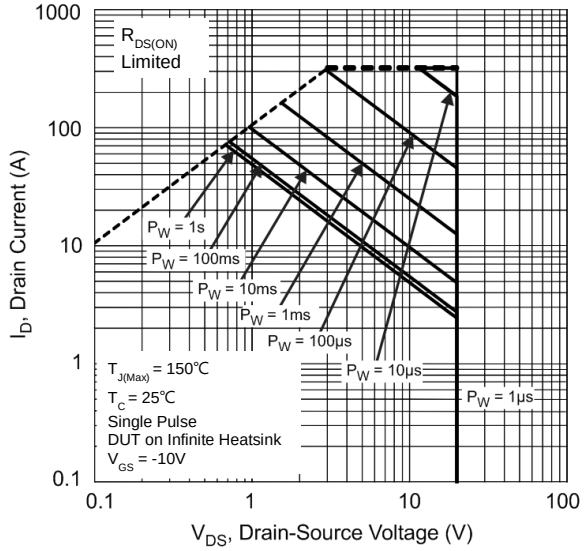


Fig. 12 SOA, Safe Operation Area

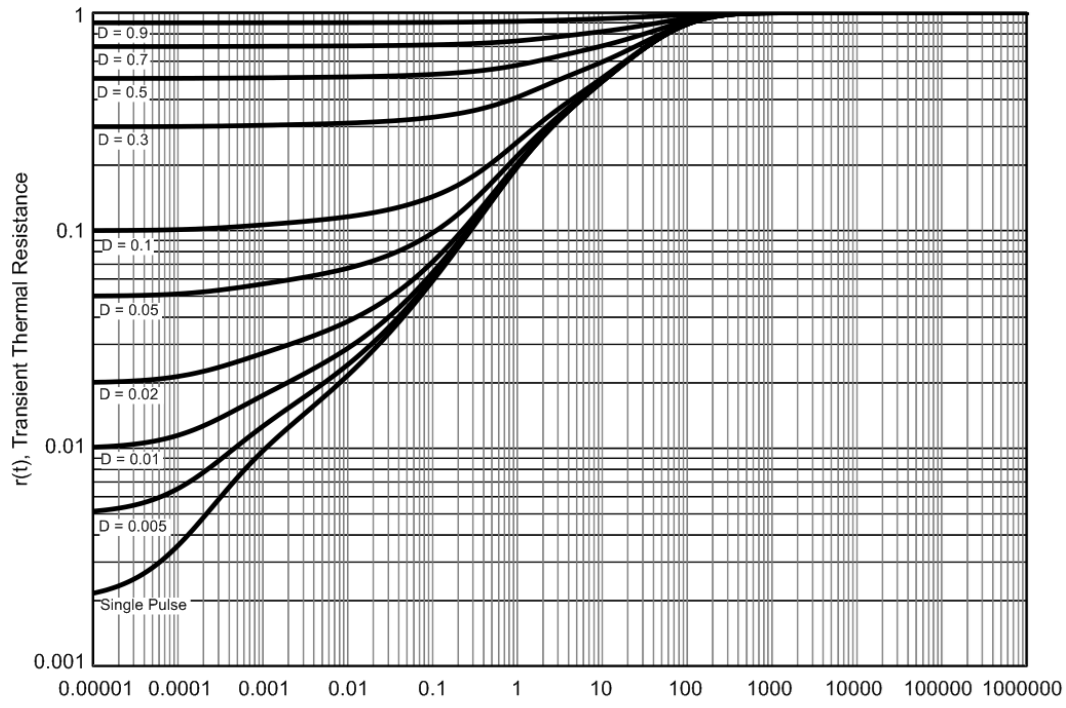
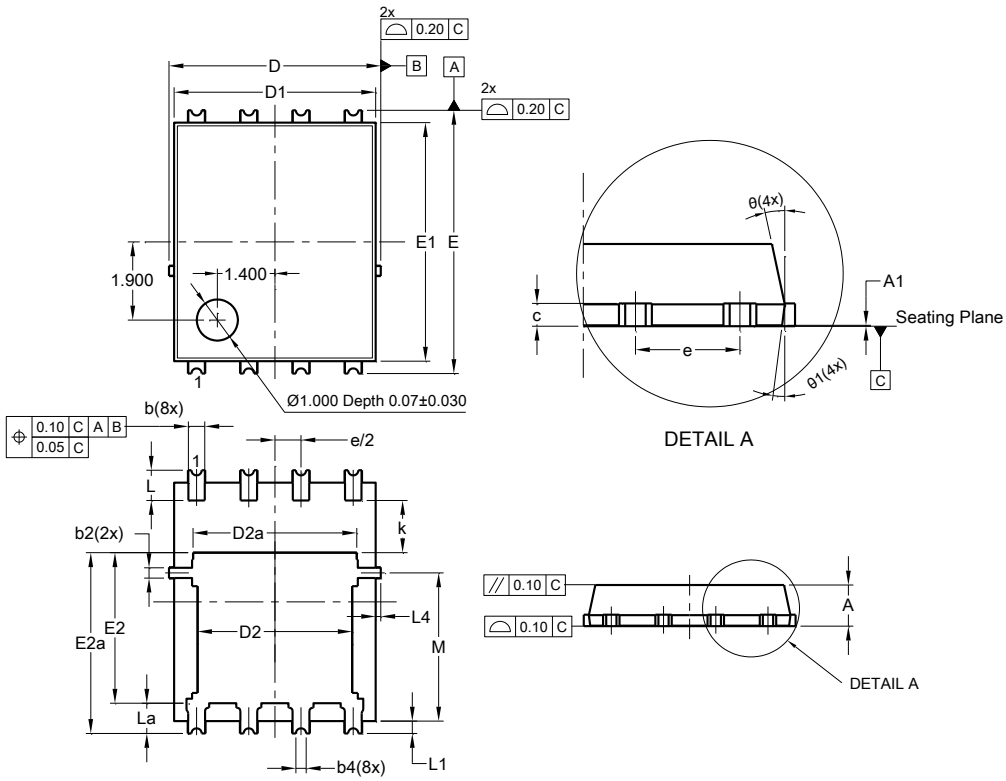


Fig. 13 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)

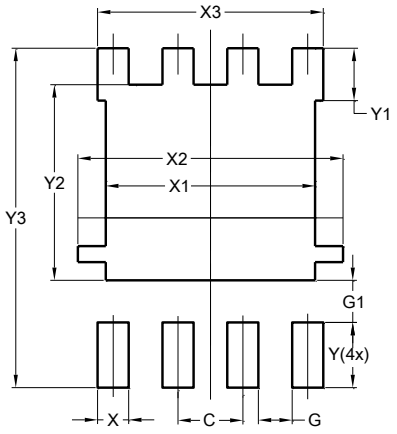


PowerDI5060-8/SWP (Type UX)			
Dim	**Min**	**Max**	**Typ**
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
X3	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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